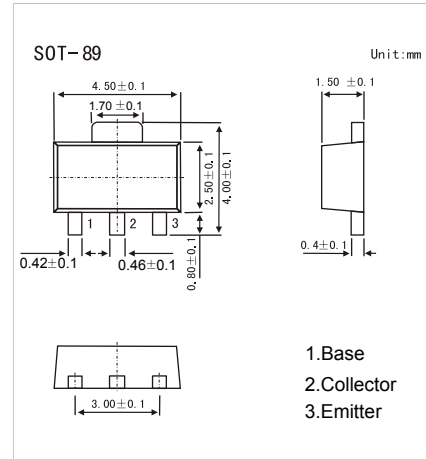


NPN Transistors

BF620

■ Features

- Low current (max. 50mA)
- High voltage (max. 300V).
- Video output stages.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	300	V
Collector - Emitter Voltage	V _{CEO}	300	
Emitter - Base Voltage	V _{EB0}	5	
Collector Current - Continuous	I _c	50	mA
Collector Power Dissipation	P _c	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 100 μA, I _E = 0	300			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = 1 mA, I _B = 0	300			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _c = 0	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 200 V, I _E = 0			100	nA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _c =0			50	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =30 mA, I _B =5mA			0.6	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =30 mA, I _B =5mA			1.2	
DC current gain	h _{FE}	V _{CE} = 20V, I _c = 25mA	50			
Transition frequency	f _T	V _{CE} = 10V, I _c = 10mA, f=100MHz	60			MHz

■ Marking

Marking	DC
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